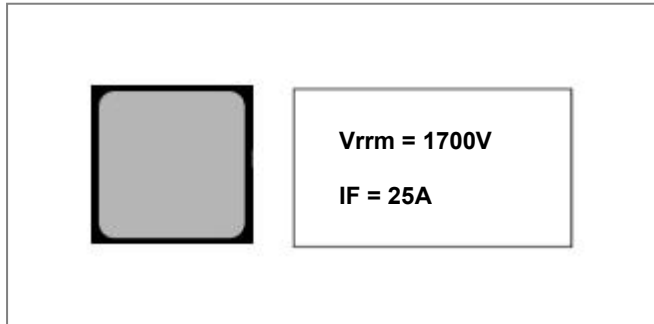


SD5-1700-S025AB

SiC Schottky Power Rectifier Chip



Description

- 1700-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

Part Number	Die Size	Anode	Cathode
SD5-1700-S025AB	4.75mm*4.75mm	Al	Ag

Maximum Ratings:

Parameter	Symbol	Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}	1700	V
Surge Peak Reverse Voltage	V _{RSM}	1700	V
DC Peak Blocking Voltage	V _R	1700	V
Maximum DC Current*	I _F	66	A
Repetitive Peak Forward Surge Current	I _{FRM}	168	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	280	A
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C

Technical Data
Data Sheet D0337, REV.-

Electrical Characteristics(T=25°C unless otherwise specified):

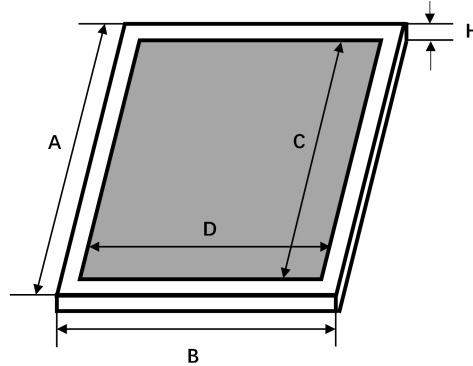
Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 25A, Pulse, T _J = 25 °C	1.55	1.8	V
	V _{F2}	@ 25A, Pulse, T _J = 175 °C	2.5	3.0	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	1	10	uA
	I _{R2}	@V _R = rated V _R , T _J = 175 °C	20	200	uA
Junction Capacitance	C _T	V _R =0V, T _J =25°C, f=1MHz	2252	-	pF
Reverse Recovery Charge	Q _c	I _F = 25A, di/dt = 200A/μs, V _R = 1700 V, T _J =25°C	279	-	nC
Capacitance Stored Energy	E _c	V _R = 1700 V, T _J = 25 °C	303	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Mechanical Parameters:

Parameter	Typ.	Unit
Die Size	4.75*4.75	mm
Anode Pad opening	3.50*3.50	mm
Thickness	350 ±25	μm
Anode Metalization (Al)	4	μm
Cathode Metalization (Ag)	0.4	μm
Frontside Passivation	Polyimide	

Chip Dimension



symbol	Dimension +/- 10%
A	4.75mm
B	4.75mm
C	3.50mm
D	3.50mm
H	350um

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